DS05-11154-1E

# MEMORY Registered 16 M × 72 BIT SYNCHRONOUS DYNAMIC RAM DIMM

# MB8516SR72CA-102/-103/-102L/-103L

168-pin, 4 Clock, 1-bank, based on 16 M × 4 Bit SDRAMs with SPD

#### **■** DESCRIPTION

The Fujitsu MB8516SR72CA is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of eighteen MB81F64442C devices which organized as four banks of 16 M  $\times$  4 bits and a 2K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8516SR72CA features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8516SR72CA is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for server system, workstations, high-end PCs, and other applications where enhanced performance is needed.

#### **■ PRODUCT LINE & FEATURES**

P	arameter		MB8516SR72CA-102/-102L	MB8516SR72CA-103/-103L			
CL-trcd-trp			2-2-2 clk min.	3-2-2 clk min.			
Clock Frequency			100 MHz max.	100 MHz max.			
Burst Mode Cycle			10ns min.	15ns min.			
Time	Mode	CL = 3*	10ns min.	10ns min.			
Output Valid from	Registered	CL = 2*	6 ns	8 ns			
Clock	Mode	CL = 3*	6 ns	6 ns			
	Two Banks Active	)	13540 mW max.				
Power Dissipation	Self Refresh Mode		495 mW max. (Std. power)				
	OCH IXCHESH WIOC		455 mW max	. (Low power)			

Note \*: For registered mode, actual CAS Latency is added one cycle to the CAS Latency of device because of a delay by registers.

- Registered 168-pin DIMM Socket Type (Lead pitch: 1.27 mm)
- Conformed to JEDEC Standard
- Organization: 16,777,216 words × 72 bits
- Memory: MB81F64442C (16 M × 4, 4-bank) × 18 pcs Serial Presence Detect (SPD) with Serial EEPROM:
- 3.3 V ±0.3 V Supply Voltage
- All input/output LVTTL compatible
- Conformed to Intel PC/100 spec

- 4096 Refresh Cycle every 65.6 ms
- Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Serial Presence Detect (SPD) with Serial EEPROM: Intel SPD spec Rev 1.2A Format
- Module size:
  - 1.70" (height)  $\times$  5.25" (length)  $\times$  0.32" (thickness)

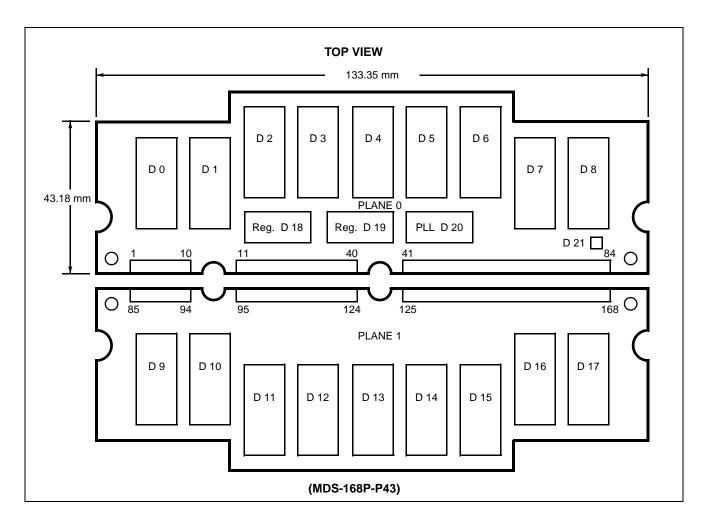
# PACKAGE 168-pin plastic DIMM (socket type) Under development (MDS-168P-P43)

#### **Package and Ordering Information**

168-pin DIMM, order as MB8516SR72CA-xxxDG (DG = Std. power ver., Gold pad)
 MB8516SR72CA-xxxLDG (LDG = Low power ver., Gold pad)

#### **■ PIN ASSIGNMENTS**

Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name
1	Vss	29	DQMB <sub>1</sub>	57	DQ <sub>18</sub>	85	Vss	113	DQMB₅	141	DQ <sub>50</sub>
2	DQ₀	30	<del>S</del> ₀	58	DQ <sub>19</sub>	86	DQ <sub>32</sub>	114	N.C.	142	DQ <sub>51</sub>
3	DQ <sub>1</sub>	31	N.C.	59	Vcc	87	DQ <sub>33</sub>	115	RAS	143	Vcc
4	DQ <sub>2</sub>	32	Vss	60	DQ <sub>20</sub>	88	DQ <sub>34</sub>	116	Vss	144	DQ <sub>52</sub>
5	DQ <sub>3</sub>	33	A <sub>0</sub>	61	N.C.	89	DQ <sub>35</sub>	117	A <sub>1</sub>	145	N.C.
6	Vcc	34	A <sub>2</sub>	62	N.C.	90	Vcc	118	<b>A</b> 3	146	N.C.
7	DQ <sub>4</sub>	35	A <sub>4</sub>	63	N.C.	91	DQ <sub>36</sub>	119	<b>A</b> 5	147	REGE
8	DQ₅	36	<b>A</b> 6	64	Vss	92	DQ <sub>37</sub>	120	A <sub>7</sub>	148	Vss
9	DQ <sub>6</sub>	37	A8	65	DQ <sub>21</sub>	93	DQ <sub>38</sub>	121	<b>A</b> 9	149	DQ <sub>53</sub>
10	DQ <sub>7</sub>	38	A <sub>10</sub>	66	DQ <sub>22</sub>	94	DQ <sub>39</sub>	122	BA <sub>0</sub>	150	DQ <sub>54</sub>
11	DQ <sub>8</sub>	39	BA <sub>1</sub>	67	DQ <sub>23</sub>	95	DQ <sub>40</sub>	123	A <sub>11</sub>	151	DQ <sub>55</sub>
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss
13	DQ <sub>9</sub>	41	Vcc	69	DQ <sub>24</sub>	97	DQ <sub>41</sub>	125	CLK <sub>1</sub>	153	DQ <sub>56</sub>
14	DQ <sub>10</sub>	42	CLK <sub>0</sub>	70	DQ <sub>25</sub>	98	DQ <sub>42</sub>	126	N.C.	154	DQ <sub>57</sub>
15	DQ <sub>11</sub>	43	Vss	71	DQ <sub>26</sub>	99	DQ <sub>43</sub>	127	Vss	155	DQ <sub>58</sub>
16	DQ <sub>12</sub>	44	N.C.	72	DQ <sub>27</sub>	100	DQ <sub>44</sub>	128	CKE <sub>0</sub>	156	DQ <sub>59</sub>
17	DQ <sub>13</sub>	45	$\overline{S}_2$	73	Vcc	101	DQ <sub>45</sub>	129	N.C.	157	Vcc
18	Vcc	46	DQMB <sub>2</sub>	74	DQ <sub>28</sub>	102	Vcc	130	DQMB <sub>6</sub>	158	DQ <sub>60</sub>
19	DQ <sub>14</sub>	47	DQMB <sub>3</sub>	75	DQ <sub>29</sub>	103	DQ <sub>46</sub>	131	DQMB <sub>7</sub>	159	DQ <sub>61</sub>
20	DQ <sub>15</sub>	48	N.C.	76	DQ <sub>30</sub>	104	DQ <sub>47</sub>	132	N.C.	160	DQ <sub>62</sub>
21	CB <sub>0</sub>	49	Vcc	77	DQ <sub>31</sub>	105	CB <sub>4</sub>	133	Vcc	161	DQ <sub>63</sub>
22	CB <sub>1</sub>	50	N.C.	78	Vss	106	CB <sub>5</sub>	134	N.C.	162	Vss
23	Vss	51	N.C.	79	CLK <sub>2</sub>	107	Vss	135	N.C.	163	CLK <sub>3</sub>
24	N.C.	52	CB <sub>2</sub>	80	N.C.	108	N.C.	136	CB <sub>6</sub>	164	N.C.
25	N.C.	53	СВз	81	N.C. (WP)	109	N.C.	137	CB <sub>7</sub>	165	SA <sub>0</sub>
26	Vcc	54	Vss	82	SDA	110	Vcc	138	Vss	166	SA <sub>1</sub>
27	WE	55	DQ <sub>16</sub>	83	SCL	111	CAS	139	DQ <sub>48</sub>	167	SA <sub>2</sub>
28	DQMB <sub>0</sub>	56	DQ <sub>17</sub>	84	Vcc	112	DQMB <sub>4</sub>	140	DQ <sub>49</sub>	168	Vcc



#### **■ PIN DESCRIPTIONS**

Symbol	I/O	Function	Symbol	I/O	Function
A <sub>0</sub> to A <sub>11</sub>	I	Address Input	DQ <sub>0</sub> to DQ <sub>63</sub>	I/O	Data Input/Data Output
BA <sub>0</sub> , BA <sub>1</sub>	I	Bank Select (Bank Address)	CB <sub>0</sub> to CB <sub>7</sub>	I/O	ECC Data Input/Output
RAS	I	Row Address Strobe	Vcc	_	Power Supply (+3.3 V)
CAS	I	Column Address Strobe	Vss	_	Ground (0 V)
WE	I	Write Enable	N.C.	_	No Connection
CLK <sub>0</sub> to CLK <sub>3</sub>	I	Clock Input	SA <sub>0</sub> to SA <sub>2</sub>	I	Serial PD Address Input
CKE₀	I	Clock Enable	SCL	I	Serial PD Clock
$\overline{S}_0$ , $\overline{S}_2$	I	Chip Select	SDA	I/O	Serial PD Address & Data Input/Output
REGE *1	I	Register Enable	WP	I	Serial PD Write Protect
DQMB <sub>0</sub> to DQMB <sub>7</sub>		Data (DQ) Mask		•	_

**Notes:** \*1. REGE pin is to switch the module function mode to Registered Mode, or Buffered Mode. For Registered Mode function, REGE = VIH.

#### **■ SERIAL-PD INFORMATION**

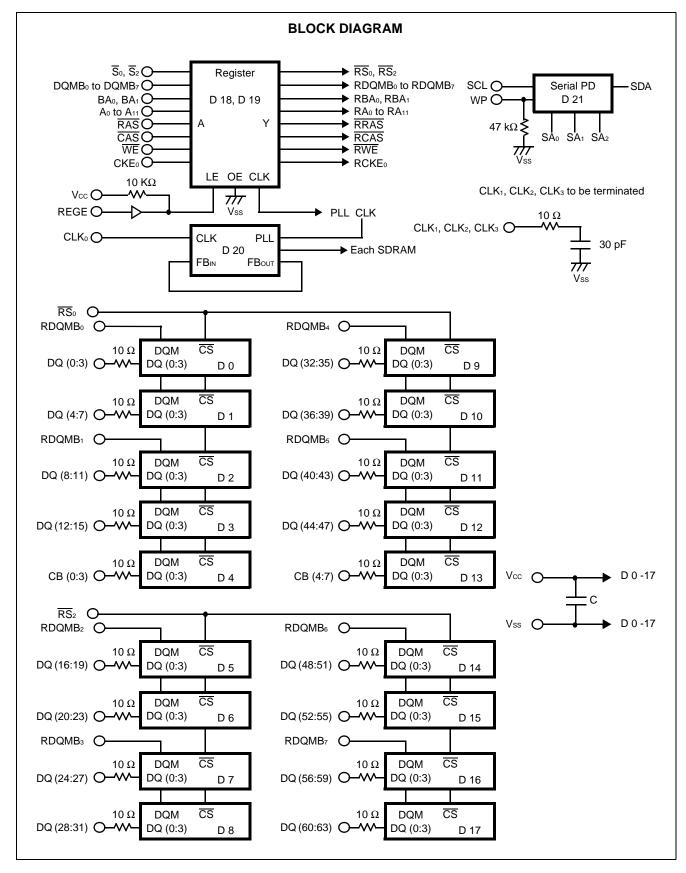
			Hex \	/alue
Byte	Function Described		-102/- 102L	-103/- 103L
0	Defines Number of Bytes Written into Serial Memory at Module	128 Byte	80h	80h
1 2 3 4 5 6 7 8	Manufacture Total Number of Bytes of SPD Memory Device Fundamental Memory Type Number of Row Addresses	256 Byte SDRAM 12	08h 04h 0Ch	08h 04h 0Ch
4	Number of Column Addresses	10	0Ah	0Ah
5	Number of Module Banks Data Width	1 bank 72 bit	01h 48h	01h 48h
ž	Data Width (Continuation)	+0	00h	00h
8	Interface Type	LVTTL	01h	01h
9	SDRAM Cycle Time (Highest CAS Latency)	10 / 10 ns	A0h	A0h
10 11	SDRAM Access from Clock (Highest CAS Latency) DIMM Configuration Type	6 / 6 ns ECC	60h 02h	60h 02h
12	Refresh Rate/Type	Self, Normal	80h	80h
13	Primary SDRAM Width	×4	04h	04h
14	Error Checking SDRAM Width	×4	04h	04h
15	Minimum Clock Delay for Back to Back Random Column Addresses	1 Cycle	01h	01h
16	Burst Lengths Supported	1, 2, 4, 8, Page 4 bank	8Fh	8Fh
17 18	Number of Banks on Each SDRAM Device CAS Latency Supported	2, 3	04h 06h	04h 06h
19	CS Latency	0	01h	01h
20	Write Latency	Ō	01h	01h
21	SDRAM Module Attributes	Registered	1Fh	1Fh
22 23	SDRAM Device Attributes: General	*1	0Eh	0Eh
23	SDRAM Cycle Time (2nd. Highest CAS Latency) SDRAM Access from Clock (2nd. Highest CAS Latency)	10 / 15 ns 6 / 8 ns	A0h 60h	F0h 80h
25	SDRAM Cycle Time (3rd. Highest CAS Latency)	No Support	00h	00h
26	SDRAM Access from Clock (3rd. Highest CAS Latency)	No Support	00h	00h
27	Minimum Row Precharge Time (trp)	20 / 20 ns	14h	14h
28	Row Activate to Row Activate Minimum (trrd)	20 / 20 ns	14h	14h
29 30	RAS to CAS Delay Min. (tRcb)	20 / 20 ns 50 / 50 ns	14h	14h 32h
31	Minimum RAS Pulse Width Module Bank Density	128 MByte	32h 20h	20h
32	Command and Address Signal Input Setup Time	2 ns	20h	20h
33	Command and Address Signal Input Hold Time	1 ns	10h	10h
34	Data Signal Input Setup Time	2 ns	20h	20h
35	Data Signal Input Hold Time	1 ns	10h	10h
36 to 61 62	Unused Storage Locations SPD Data Revision Code	1.2	00h 12h	00h 12h
63	Checksum for Byte 0 to 62	*2	3Fh	AFh
64 to 71	Manufacturer's JEDEC ID Code Per JEP-108E	Optional	00h	00h
72	Manufacturing Location	Optional	00h	00h
73 to 90	Manufacturer's Part Number	Optional	00h	00h
91 to 92 93 to 94	Revision Code Manufacturing Data	Optional Optional	00h 00h	00h 00h
95 to 98	Assembly Serial Number	Optional	00h	00h
99 to 125	Manufacturer Specific Data	Optional	00h	00h
126	Intel Specification Frequency	100 MHz	64h	64h
127	Intel Specification Details for 100 MHz Support	CL = 2, 3 / 3	8Fh	8Dh
128+	Unused Storage Locations	_		

Note: Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

#### \*1. Byte 22: SDRAM Device Attributes

,							
Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
TBD	TBD	Upper Vcc tolerance	Lower Vcc tolerance	Supports Write 1 /Read Burst	Supports Precharge All	Supports Auto- Precharge	Supports Early RAS Precharge
0	0	0	0	1	1	1	0

\*2. Byte 63: Checksum for Byte 0 to 62
This byte is the checksum for Byte 0 through 62. This byte contains the value of the low 8-bits of the arithmetic sum of Byte 0 through 62.



#### ■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Va	lue	Unit
Farameter	Symbol	Min.	Max.	Onit
Supply Voltage*	Vcc	-0.5	+4.6	V
Input Voltage*	Vin	-0.5	+4.6	V
Output Voltage*	Vоит	-0.5	+4.6	V
Storage Temperature	Тѕтс	<b>–</b> 55	+125	°C
Power Dissipation	PD	_	21	W
Output Current (D.C.)	Іоит	<b>-</b> 50	+50	mA

<sup>\*:</sup> Voltages referenced to Vss (= 0 V)

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

#### ■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol		Unit		
Farameter	Notes	Symbol	Min.	Тур.	Max.	Ullit
Supply Voltage	*1	Vcc	3.0	3.3	3.6	V
Supply Voltage	I	Vss	0	0	0	V
Input High Voltage, All Inputs	*1, 2	ViH	2.0	_	Vcc +0.5	V
Input Low Voltage, All Inputs	*1, 3	VIL	-0.5	_	0.8	V
Ambient Temperature		TA	0	_	+70	°C

<sup>\*1.</sup> Voltages referenced to Vss (=0V)

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

> Always use semiconductor devices within their recommended operating conditionranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

> No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

<sup>\*2.</sup> Overshoot limit:  $V_{H}$  (max.) =  $V_{CC}$  +1.5 V with a pulse-width  $\leq 5$  ns.

<sup>\*3.</sup> Undershoot limit:  $V_{\perp}$  (min.) = -1.5 V with a pulse-width  $\leq 5$  ns.

#### **■ CAPACITANCE**

 $(Vcc = +3.3 \text{ V}, f = 1 \text{ MHz}, T_A = +25^{\circ}\text{C})$ 

Paramet	O.F.	Symbol	Va	lue	Unit
Paramet	er	Symbol	Min.	Max.	Onit
	A <sub>0</sub> to A <sub>11</sub> , BA <sub>0</sub> , BA <sub>1</sub>	C <sub>IN1</sub>	_	8	pF
	RAS, CAS, WE	C <sub>IN2</sub>	_	9	pF
	$\overline{S}_0$ , $\overline{S}_2$	Сімз	_	10	pF
	CKE <sub>0</sub>	C <sub>IN4</sub>	_	14	pF
Input Capacitance	CLK <sub>0</sub> to CLK <sub>3</sub>	C <sub>IN5</sub>	_	38	pF
	DQMB <sub>0</sub> to DQMB <sub>7</sub>	C <sub>IN6</sub>	_	9	pF
	SCL	C <sub>IN7</sub>	_	5	pF
	SA <sub>0</sub> , SA <sub>1</sub> , SA <sub>2</sub>	CIN8	_	6	pF
	REGE	C <sub>IN9</sub>	_	23	pF
	SDA	CSDA	_	6	pF
Input/Output Capacitance	DQ <sub>0</sub> to DQ <sub>63</sub>	CDQ	_	13	pF
	CB <sub>0</sub> to CB <sub>7</sub>	Ссв	_	13	pF

#### **■ DC CHARACTERISTICS**

(At recommended operating conditions unless otherwise noted.) Notes 1, 2, 3

Parameter	Notes	Symbol	Condition		Ma	ax.	Unit
		<b>-</b>	<b>CO.G.</b>	Min.	Std. ver.	Low ver.	
Operating Current			Burst Length = 1, tRC = min  for BL = 1, tCK = min, One Bank Active, Outputs Open, Address changed up to 1 time during $tCK(min.)$ , $0 \text{ V} \leq VIN \leq VIL \text{ max}$ $VIH min \leq VIN \leq VCC$	_	21	mA	
(Average Power Supply Current)	*4 -	Ісств	Burst Length = 1 (each Bank), $t_{RC}$ = min for BL = 1 (each Bank), $t_{CK}$ = min, Two Banks Active, Outputs Open, Address changed up to 1 time during $t_{CK}$ (min.), $0 \ V \le V_{IN} \le V_{IL}$ max $V_{IH}$ min $\le V_{IN} \le V_{CC}$	_	3760		mA
		Ісс2Р	CKE = V <sub>IL</sub> , tc <sub>K</sub> = min, All Banks Idle, Power Down Mode, $0 \text{ V} \leq \text{V}_{\text{IN}} \leq \text{V}_{\text{IL}} \max$ V <sub>IH</sub> min $\leq \text{V}_{\text{IN}} \leq \text{V}_{\text{CC}}$	_	155	137	mA
		Icc2PS	$\label{eq:cke} \begin{split} CKE &= V_{\text{IL}}, \\ CLK &= V_{\text{IH}} \text{ or } V_{\text{IL}}, \\ All \text{ Banks Idle,} \\ \text{Power Down Mode,} \\ 0  V \leq V_{\text{IN}} \leq V_{\text{IL}} \text{ max} \\ V_{\text{IH}} \text{ min} \leq V_{\text{IN}} \leq V_{\text{CC}} \end{split}$	_	137	128	mA
Precharge Standby Current (Power Supply Current)	*4	Ісс2N	CKE = $V_{IH}$ , $t_{CK}$ = min, All Banks Idle, NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, 0 V $\leq$ V <sub>IN</sub> $\leq$ V <sub>IL</sub> max V <sub>IH</sub> min $\leq$ V <sub>IN</sub> $\leq$ V <sub>CC</sub>	_	390		mA
		Icc2NS	CKE = VIH, CLK = VIH or VIL, All Banks Idle, Input Signals are Stable, $0 \text{ V} \leq \text{VIN} \leq \text{VIL} \max$ VIH min $\leq \text{VIN} \leq \text{VCC}$	_	155		mA

(Continued)

### (Continued)

				Value			
Parameter I	Notes	Symbol	Condition		Ма	ax.	Unit
		<b></b>	0000000	Min.	Std. ver.	Low ver.	
		Іссзр	CKE = VIL, tck = min, Any Bank Active, $0 \text{ V} \leq \text{VIN} \leq \text{VIL max}$ VIH min $\leq \text{VIN} \leq \text{VCC}$	_	155	137	mA
Active Standby Current  *4 (Power Supply Current)		Іссзрѕ	$\label{eq:cke} \begin{split} & CKE = V_{IL}, \\ & CLK = V_{IH} \ or \ V_{IL}, \\ & Any \ Bank \ Active, \\ & 0 \ V \leq V_{IN} \leq V_{IL} \ max \\ & V_{IH} \ min \leq V_{IN} \leq V_{CC} \end{split}$	_	137	128	mA
		Іссэн	CKE = VIH, tck = min, Any Bank Active, NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, $0 \text{ V} \leq \text{VIN} \leq \text{VIL} \max$ VIH min $\leq \text{VIN} \leq \text{VCC}$	_	57	70	mA
		Іссзиѕ	$\label{eq:cke} \begin{split} CKE &= V_IH, \\ CLK &= V_IH \text{ or } V_IL, \\ Any Bank Active, \\ 0 \ V &\leq V_IN &\leq V_IL \text{ max} \\ V_IH \ min &\leq V_IN &\leq V_CC \end{split}$	_	155		mA
Burst Mode Current *4 (Average Power Supply Current)		Icc4	tcк = min, Gapless data, Burst Length = 4, Outputs open, Multiple-banks Active, $0 \ V \le V_{IN} \le V_{IL} \max$ $V_{IH} \min \le V_{IN} \le V_{CC}$	_	— 1835		mA
Auto-refresh Current (Average Power Supply Current)	*4	Icc5	Auto Refresh, $t_{\text{CK}} = \text{min}, \\ t_{\text{RC}} = \text{min}, \\ 0 \ V \le V_{\text{IN}} \le V_{\text{IL}} \text{max} \\ V_{\text{IH}} \ \text{min} \le V_{\text{IN}} \le V_{\text{CC}}$	_	— 4456		mA
Self-refresh Current (Average Power Supply Current) *4		Icc6	Self-refresh, tc $\kappa$ = min, CKE $\leq$ 0.2 V, 0 V $\leq$ V <sub>IN</sub> $\leq$ V <sub>IL</sub> max V <sub>IH</sub> min $\leq$ V <sub>IN</sub> $\leq$ V <sub>CC</sub>	_	137	128	mA
Input Leakage Current Others		I	0 V ≤ V <sub>IN</sub> ≤ V <sub>CC</sub> All other pins not	-50	5	0	^
		lц	under test = 0 V	-10	1	0	μΑ
Output Leakage Current		ILO	Output is disabled (Hi-Z) 0 V ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	-10	10		μΑ
LVTTL Output High Voltage	*5	Vон	I <sub>OH</sub> = -2.0 mA 2.4 —		_	V	
LVTTL Output Low Voltage	*5	$V_{OL}$	IoL = +2.0 mA	_	0	.4	V

**Notes:** \*1. An initial pause (DESL on NOP) of 200 μs is required after power-on followed by a minimum of eight Auto-refresh cycles.

- \*2. Values of Icc1s, Icc1D and Icc4 are for when one side of the double-sided module is in standby mode (Icc2N) and the other side is in active.
- \*3. DC characteristics is the Serial PD standby state (V<sub>IN</sub> = GND or V<sub>CC</sub>).
- \*4. lcc depends on the output termination, load conditions, clock cycle rate and signal clock rate. The specified values are obtained with the output open and no termination resistors.
- \*5. Voltages referenced to Vss (= 0 V)

#### **■ AC CHARACTERISTICS**

(SDRAM Component Specifications) Notes 1, 2, 3

#### (1) BASE CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

No.	Parameter	Not	Notes		MB8516 -102/	SR72CA -102L		SR72CA -103L	Unit
					Min.	Max.	Min.	Max.	
1	Clock Period	*4	CL = 2	tck2	10	_	15	_	ns
1	Clock Fellod	4	CL = 3	<b>t</b> cкз	10	_	10	_	113
2	Clock High Time		tсн	3	_	3	_	ns	
3	Clock Low Time				3	_	3	_	ns
4	Input Setup Time	Registere	d Mode	tsı	3.5	_	3.5	_	ns
5	Input Hold Time	Registere	d Mode	tнı	2.5	_	2.5	_	ns
6	Output Valid from Clock	*4, *5, *6	CL = 2	t <sub>AC2</sub>	_	6	_	8	ns
	(tck = min)	4, 5, 6	CL = 3	<b>t</b> AC3	_	6	_	6	115
7	Output in Low-Z			tız	0	_	0	_	ns
8	Output in Lligh 7	*4, *7	CL = 2	t <sub>HZ2</sub>	3	6	3	8	20
0	Output in High-Z	4, 7	CL = 3	<b>t</b> HZ3	3	6	3	6	ns
9	Output Hold Time			tон	3	_	3	_	ns
10	Time between Refresh			tref	_	65.6	_	65.6	ms
11	Transition Time			<b>t</b> ⊤	0.5	2	0.5	2	ns
12	CKE Setup Time for Power Down Exit Time	Registere	d Mode	<b>t</b> cksp	3.5	_	3.5	_	ns

#### (2) BASE VALUES FOR CLOCK COUNT/LATENCY

No.	Parameter	Not	es	Symbol	MB85169 -102/-103/-1	SR72CA 102L/-103L	Unit
				•	Min.	Max.	
1	RAS Cycle Time		*8	<b>t</b> RC	70	_	ns
2	RAS Precharge Time			<b>t</b> RP	20	_	ns
3	RAS Active Time			<b>t</b> RAS	50	110000	ns
4	RAS to CAS Delay Time		*9	<b>t</b> RCD	20	_	ns
5	Write Recovery Time			<b>t</b> wr	10	_	ns
6	Data-in to Precharge Lead Time			<b>t</b> DPL	10	_	ns
7	Data-in to Active/Refresh Command Period	*4	CL = 2	<b>t</b> DAL2	1 cyc + t <sub>RP</sub>	_	nc
'	Data-in to Active/Reflesh Command Feriod		CL = 3	<b>t</b> DAL3	2 cyc + t <sub>RP</sub>	_	ns
8	Mode Register Set Cycle Time			<b>t</b> RSC	20	_	ns
9	RAS to RAS Bank Active Delay Time			<b>t</b> rrd	20	_	ns

#### (3) CLOCK COUNT FORMULA (\*10)

$$Clock \ge \frac{\text{Base Value}}{\text{Clock Period}} \text{ (Round off a whole number)}$$

#### (4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

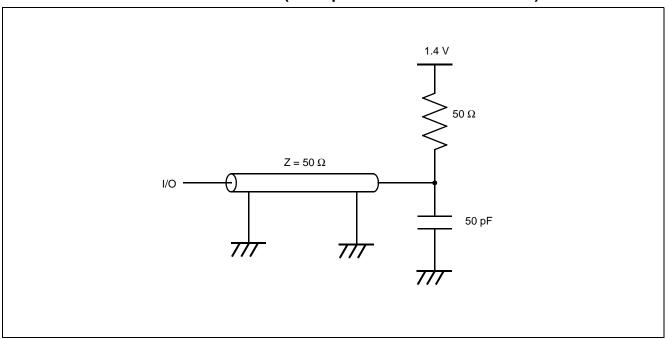
No.	Parameter		Notes	Symbol	MB8516SR72CA -102/-103/-102L/-103L	Unit	
					Registered Mode		
1	CKE to Clock Disable			Іске	2	Cycle	
2	DQM to Output in High-Z			I <sub>DQZ</sub>	3	Cycle	
3	DQM to Input Data Delay			IDQD	1	Cycle	
4	Last Output to Write Command Delay			lowd	1	Cycle	
5	Write Command to Input Data Delay			IDWD	1	Cycle	
_	Durch and to Outrot in High 7 Dalan	*4	CL = 2	IROH2	3	Cyrolo	
6	Precharge to Output in High-Z Delay	4	CL = 3	Ігонз	4	Cycle	
7	Burst Stop Command to Output in High-Z Delay	*4	CL = 2	BSH2	3	Cycle	
/			CL = 3	<b>І</b> вѕнз	4		
8	CAS to CAS Delay (min)			Iccd	1	Cycle	
9	CAS Bank Delay (min)			Ісво	1	Cycle	

- **Notes:** \*1. An initial pause (DESL on NOP) of 200 μs is required after power-up followed by a minimum of eight Auto-refresh cycles.
  - \*2. 1.4 V or V<sub>REF</sub> is the reference level for measuring timing of signals. Transition times are measured between V<sub>IH</sub> (min) and V<sub>IL</sub> (max).
  - \*3. AC characteristics assume  $t_T = 1$  ns and 50 pF of capacitance load.
  - \*4. For Registered Mode, actual CAS Latency is added one cycle to the CAS Latency of this value because of a delay by registers.
  - \*5. Assumes tRCD is satisfied.
  - \*6. tac also specifies the access time at burst mode except for first access.
  - \*7. Specified where output buffer is no longer driven.
  - \*8. Actual clock count of trc (Irc) will be sum of clock count of tras (Iras) and trp (Irp).
  - \*9. Operation within the trcd (min) ensures that access time is determined by trcd (min) +tac (max); if trcd is greater than the specified trcd (min), access time is determined by trac.
  - \*10. All base values are measured from the clock edge at the command input to the clock edge for the next command input.

All clock counts are calculated by a simple formula:

clock count equals base value divided by clock period (round off to a whole number).

#### ■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



<sup>\*</sup>Source: See MB81F64442C Data Sheet for details on the electrical.

#### ■ SERIAL PRESENCE DETECT(SPD) FUNCTION

#### 1. PIN DESCRIPTIONS

#### **SCL (Serial Clock)**

SCL input is used to clock all data input/output of SPD.

#### SDA (Serial Data)

SDA is a common pin used for all data input/output of SPD. The SDA pull-up resistor is required due to the open-drain output.

#### SA<sub>0</sub>, SA<sub>1</sub>, SA<sub>2</sub> (Address)

Address inputs are used to set the least significant three bits of the eight bits slave address. The address inputs must be fixed to select a particular module and the fixed address of each module must be different each other.

#### 2. SPD OPERATIONS

#### **CLOCK and DATA CONVENTION**

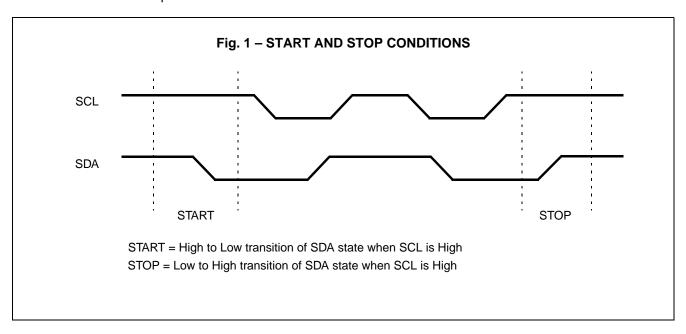
Data states on the SDA can change only during SCL= Low. SDA state changes during SCL = High are indicated start and stop conditions. Refer to Fig. 1 below.

#### START CONDITION

All commands are preceded by a start condition, which is a transition of SDA state from High to Low when SCL = High. SPD will not respond to any command until this condition has been met.

#### **STOP CONDITION**

All read or write operation must be terminated by a stop condition, which is a transition of SDA state from Low to High when SCL = High. The stop condition is also used to make the SPD into the state of standby power mode after a read sequence.



#### **ACKNOWLEDGE**

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

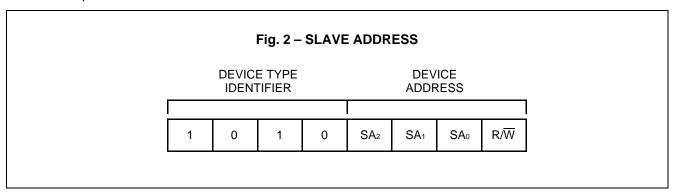
#### SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig. 2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices —namely up to eight modules— on the bus. The eight addresses for eight SPD devices are defined by the state of the  $SA_0$ ,  $SA_1$  and  $SA_2$  inputs.

The last bit of the slave address defines the operation to be performed. When  $R/\overline{W}$  bit is "1", a read operation is selected, when  $R/\overline{W}$  bit is "0", a write operation is selected.

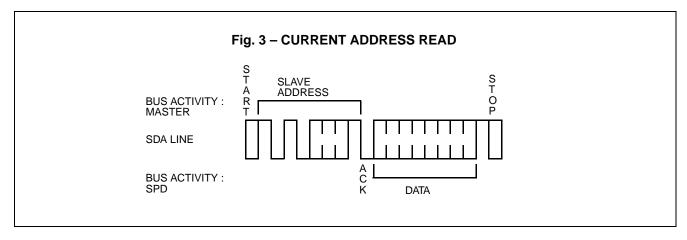
Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of  $SA_0$ ,  $SA_1$ , and  $SA_2$  inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the  $R/\overline{W}$  bit, the SPD will execute a read or write operation.



#### 3. READ OPERATIONS

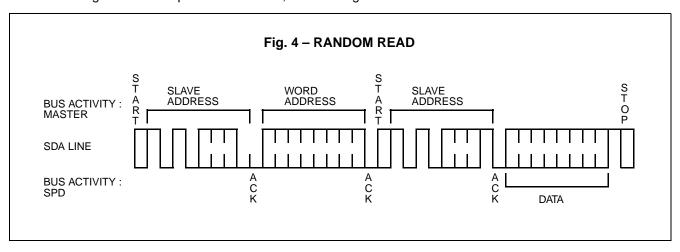
#### **CURRENT ADDRESS READ**

Internally the SPD contains an address counter that maintains the address of the last data accessed, incriminated by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the R/W bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 3 for the sequence of address, acknowledge and data transfer.



#### **RANDOM READ**

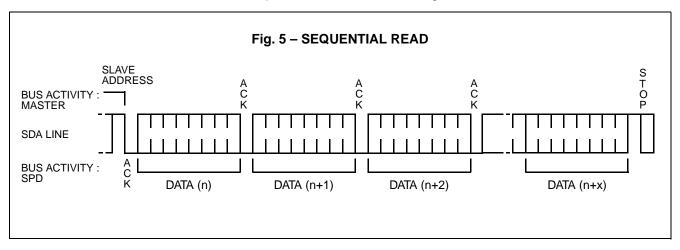
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the  $R/\overline{W}$  bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the  $R/\overline{W}$  bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 4 for the sequence of address, acknowledge and data transfer.



#### **SEQUENTIAL READ**

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter "rolls over" to address 0 and the SPD continues to output data for each acknowledge received.



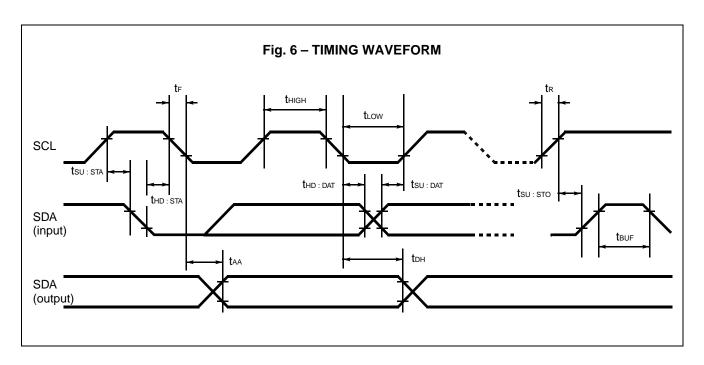
#### 4. DC CHARACTERISTICS

Parameter	Note	Symbol	Condition	Value		Unit
Parameter	Note	Symbol	Min.		Max.	
Input Leakage Current		Sılı	$0 \text{ V} \leq V_{IN} \leq V_{CC}$	-10	10	μΑ
Output Leakage Current		SILO	0 V ≤ Vouт ≤ Vcc	-10	10	μΑ
Output Low Voltage	*1	Svol	IoL = 3.0 mA	_	0.4	V

Note: \*1. Referenced to Vss.

#### 5. AC CHARACTERISTICS

Na	Parameter	Comple of	Va	11:4	
No.		Symbol	Min.	Max.	Unit
1	SCL Clock Frequency	fscL	_	100	KHz
2	Noise Suppression Time Constant at SCL, SDA Inputs	Tı	_	100	ns
3	SCL Low to SDA Data Out Valid	<b>t</b> AA	_	3.5	μs
4	Time the Bus Must Be Free Before a New Transmission Can Start	<b>t</b> BUF	4.7	_	μs
5	Start Condition Hold Time	thd:sta	4.0	_	μs
6	Clock Low Period	tLow	4.7	_	μs
7	Clock High Period	<b>t</b> HIGH	4.0	_	μs
8	Start Condition Setup Time	tsu:sta	4.7	_	μs
9	Data in Hold Time	thd:dat	0	_	μs
10	Data in Setup Time	tsu:dat	250	_	ns
11	SDA and SCL Rise Time	<b>t</b> R	_	1	μs
12	SDA and SCL Fall Time	t⊧	_	300	ns
13	Stop Condition Setup Time	<b>t</b> su:sto	4.7	_	μs
14	Data Out Hold Time	tон	100	_	ns
15	Write Cycle Time	twr	_	15	ms



#### **■ PACKAGE DIMENSIONS**

168-pin plastic DIMM (socket type) (MDS-168P-P43)		
	Under development	
		Dimension in mm (inches)

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